







OPA376-Q1, OPA2376-Q1, OPA4376-Q1 SBOS549C - APRIL 2011 - REVISED MARCH 2021

# OPAx376-Q1 Low-Noise, Low Quiescent Current, Precision e-trim™ Operational Amplifiers

## 1 Features

- AEC-Q100 qualified for automotive applications:
  - Temperature grade 1: –40°C to +125°C, T<sub>△</sub>
- Functional-Safety Capable
  - Documentation available to aid functional safety system design (OPA376-Q1 and OPA2376-Q1)
- Low noise: 7.5 nV/√Hz at 1 kHz 0.1-Hz to 10-Hz noise: 0.8  $\mu$ V<sub>PP</sub> Quiescent current: 760 µA (typical)
- Low offset voltage: 5 µV (typical)
- Gain bandwidth product: 5.5 MHz
- Rail-to-rail input and output
- Single-supply operation
- Supply voltage: 2.2 V to 5.5 V
- Space-saving packages:
  - SC70, SOT-23, VSSOP, TSSOP

# 2 Applications

- Onboard (OBC) and wireless charger
- Inverter and motor control
- DC/DC converter
- Battery management system (BMS)

# 3 Description

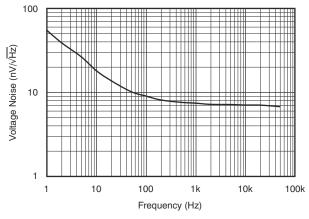
The OPAx376-Q1 family represents a new generation of low-noise e-trim<sup>™</sup> operational amplifiers, offering outstanding dc precision and ac performance. Rail-torail output, low offset (25 µV maximum), low noise  $(7.5 \text{ nV}/\sqrt{\text{Hz}})$ , quiescent current of 950 µA (maximum), and a 5.5-MHz bandwidth make this device very attractive for a variety of precision and portable applications. In addition, this device has a reasonably wide supply range with excellent PSRR, making the OPA376-Q1 an excellent choice for applications that run directly from batteries without regulation.

The OPA376-Q1 (single version) is available in MicroSIZE SC70-5, SOT23-5, and SOIC-8 packages. The OPA2376-Q1 (dual) is offered in the SOIC-8 and VSSOP-8 package. The OPA4376-Q1 (quad) is offered in a TSSOP-14 package. All versions are specified for operation from -40°C to +125°C.

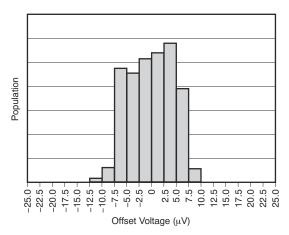
#### **Device Information**

PART NUMBER	PACKAGE <sup>(1)</sup>	BODY SIZE (NOM)				
	SC70 (5)	2.00 mm × 1.25 mm				
OPA376-Q1	SOT-23 (5)	2.90 mm × 1.60 mm				
	SOIC (8)	4.90 mm × 3.91 mm				
OPA2376-Q1	SOIC (8)	4.90 mm × 3.91 mm				
OPA2376-Q1	VSSOP (8)	3.00 mm × 3.00 mm				
OPA4376-Q1	TSSOP (14)	5.00 mm × 4.40 mm				

For all available packages, see the orderable addendum at the end of the data sheet.



Input Voltage Noise Spectral Density



Offset Voltage Production Distribution

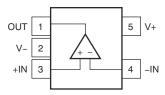


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# **5 Pin Configuration and Functions**



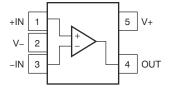
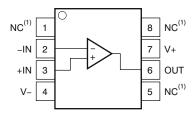


Figure 5-1. OPA376-Q1: DBV (5-Pin SOT-23)
Package, Top View

Figure 5-2. OPA376-Q1: DCK (5-Pin SC70) Package, Top View



(1) NC denotes no internal connection.

Figure 5-3. OPA376-Q1: D (8-Pin SOIC) Package, Top View

Table 5-1. Pin Functions: OPA376-Q1

		PIN				
NAME	NO.			I/O	DESCRIPTION	
INAIVIE	SOT-23	SC70	SOIC	]		
+IN	3	1	3	I	Noninverting input <sup>+</sup>	
-IN	4	3	2	ı	Inverting input	
NC	_	_	1, 5, 8	_	No internal connection	
OUT	1	4	6	0	Output	
V+	5	5	7	_	Positive (highest) power supply <sup>+</sup>	
V-	2	2	4	_	Negative (lowest) power supply	



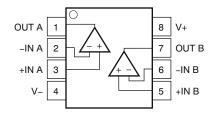


Figure 5-4. OPA2376-Q1: D (8-Pin SOIC) and DGK (8-Pin VSSOP) Packages, Top View

Table 5-2. Pin Functions: OPA2376-Q1

P	PIN		DESCRIPTION		
NAME	NO.	- I/O	DESCRIPTION		
+IN A	3	I	Noninverting input, channel A <sup>+</sup>		
−IN A	2	I	Inverting input, channel A <sup>-</sup>		
+IN B	5	I	Noninverting input, channel B <sup>+</sup>		
–IN B	6	I	Inverting input, channel B <sup>-</sup>		
OUT A	1	0	Output, channel A		
OUT B	7	0	Output, channel B		
V-	4	_	Negative (lowest) power supply		
V+	8	_	Positive (highest) power supply		



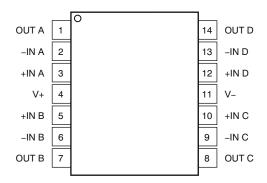


Figure 5-5. OPA4376-Q1: PW (14-Pin TSSOP) Package, Top View

Table 5-3. Pin Functions: OPA4376-Q1

F	PIN		DECODIDATION			
NAME	NO.	I/O	DESCRIPTION			
+IN A	3	I	Noninverting input, channel A <sup>+</sup>			
–IN A	2	I	nverting input, channel A <sup>-</sup>			
+IN B	5	I	nverting input, channel B <sup>+</sup>			
–IN B	6	I	rting input, channel B <sup>-</sup>			
+IN C	10	I	inverting input, channel C <sup>+</sup>			
-IN C	9	I	overting input, channel C <sup>-</sup>			
+IN D	12	I	Noninverting input, channel D <sup>+</sup>			
–IN D	13	I	Inverting input, channel D <sup>-</sup>			
OUT A	1	0	Output, channel A			
OUT B	7	0	Output, channel B			
OUT C	8	0	Output, channel C			
OUT D	14	0	Output, channel D			
V+	4	_	Positive (highest) power supply			
V–	11		Negative (lowest) power supply			



# **6 Specifications**

# **6.1 Absolute Maximum Ratings**

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
V <sub>S</sub> = (V+) - (V-)	Supply voltage		7	V
	Signal input pin voltage <sup>(2)</sup>	(V-) - 0.5	(V+) + 0.5	V
	Signal input pin current <sup>(2)</sup>	-10	10	mA
	Output short-circuit current <sup>(3)</sup>	Contin	uous	
T <sub>A</sub>	Operating temperature	-40	125	°C
TJ	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.5 V beyond the supply rails must be current limited to 10 mA or less.
- (3) Short-circuit to ground, one amplifier per package.

#### 6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 <sup>(1)</sup> HBM ESD classification level 3A	±4000	V
V <sub>(ESD)</sub>	Electrostatic discriarge	Charged-device model (CDM), per AEC Q100-011 CDM ESD classification level C6	±1000	V

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

# **6.3 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V <sub>S</sub> = (V+) - (V-)	Supply voltage	2.2 (±1.1)	5.5 (±2.75)	V
T <sub>A</sub>	Operating temperature	-40	150	°C



### 6.4 Thermal Information: OPA376-Q1

			OPA376-Q1		
	THERMAL METRIC(1)	DCK (SC70)	DBV (SOT-23)	D (SOIC)	UNIT
		5 PINS	5 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	267	273.8	100.1	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	80.9	126.8	42.4	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	54.8	85.9	41	°C/W
ΨЈТ	Junction-to-top characterization parameter	1.2	10.9	4.8	°C/W
ΨЈВ	Junction-to-board characterization parameter	54.1	84.9	40.3	°C/W
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	n/a	n/a	n/a	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

## 6.5 Thermal Information: OPA2376-Q1

		OPA2	376-Q1	
	THERMAL METRIC(1)	D (SOIC)	DGK (VSSOP)	UNIT
		8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	111.1	171.2	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	54.7	63.9	°C/W
R <sub>0JB</sub>	Junction-to-board thermal resistance	51.7	92.8	°C/W
ΨЈТ	Junction-to-top characterization parameter	10.5	9.2	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	51.2	91.2	°C/W
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	n/a	n/a	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

# 6.6 Thermal Information: OPA4376-Q1

		OPA4376-Q1	
	THERMAL METRIC <sup>(1)</sup>	PW (TSSOP)	UNIT
		14 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	107.8	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	29.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	52.6	°C/W
ΨЈТ	Junction-to-top characterization parameter	1.5	°C/W
ΨЈВ	Junction-to-board characterization parameter	51.6	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	n/a	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.



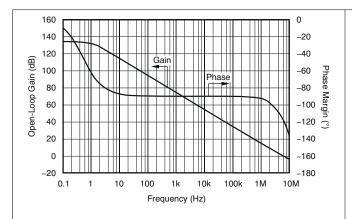
#### 6.7 Electrical Characteristics

at  $T_A = 25^{\circ}C$ ,  $R_L = 10 \text{ k}\Omega$  connected to  $V_S / 2$ ,  $V_{CM} = V_S / 2$ , and  $V_{OUT} = V_S / 2$  (unless otherwise noted)

	PARAMETER	TEST CONDITION	ONS	MIN	TYP	MAX	UNIT
OFFSET	VOLTAGE						
Vos	Input offset voltage				5	25	μV
-1) / / !	Input offset voltage versus	T <sub>A</sub> = -40°C to +85°C			0.26	1	μV/°C
dV <sub>OS</sub> /dT	temperature	T <sub>A</sub> = -40°C to +125°C			0.32	2	μV/°C
DODD	Input offset voltage versus	V <sub>S</sub> = 2.2 V to 5.5 V,	T <sub>A</sub> = 25°C		5	20	μV/V
PSRR	power supply	$V_{CM} < (V+) - 1.3 V$	$T_A = -40^{\circ}\text{C to } +125^{\circ}\text{C}$		5		μV/V
	Channel separation, dc (dual, quad)				0.5		μV/V
INPUT B	IAS CURRENT						
		T <sub>A</sub> = 25°C			0.2	10	pA
I <sub>B</sub>	Input bias current	T <sub>A</sub> = -40°C to +125°C		See	Section 6.8		pA
I <sub>os</sub>	Input offset current				0.2	10	pA
NOISE						1	
	Input voltage noise	f = 0.1 Hz to 10 Hz			0.8		μV <sub>PP</sub>
e <sub>n</sub>	Input voltage noise density	f = 1 kHz			7.5		nV/√ <del>Hz</del>
i <sub>n</sub>	Input current noise	f = 1 kHz			2		fA/√ <del>Hz</del>
INPUT V	OLTAGE			L		I	
V <sub>CM</sub>	Common-mode voltage	See Figure 6-8		(V-) - 0.1		(V+) + 0.1	V
CMRR	Common-mode rejection ratio	(V-) < V <sub>CM</sub> < (V+) - 1.3 V		76	90		dB
INPUT C	APACITANCE			1		'	
	Differential				6.5		pF
	Common-mode				13		pF
OPEN-LO	OOP GAIN			1			
٨	Onen leen veltege gein	50 mV < V <sub>O</sub> < (V+) – 50 mV, R <sub>L</sub> = 10 k	Ω	120	134		dB
A <sub>OL</sub>	Open-loop voltage gain	100 mV < V <sub>O</sub> < (V+) – 100 mV, R <sub>L</sub> = 2	kΩ	120	126		dB
FREQUE	NCY RESPONSE						
GBW	Gain-bandwidth product	C <sub>L</sub> = 100 pF, V <sub>S</sub> = 5.5 V			5.5		MHz
SR	Slew rate	G = 1, C <sub>L</sub> = 100 pF, V <sub>S</sub> = 5.5 V			2		V/µs
	Cattling time	0.1%, 2-V Step , G = 1, C <sub>L</sub> = 100 pF, \	/ <sub>S</sub> = 5.5 V		1.6		μs
t <sub>S</sub>	Settling time	0.01%, 2-V Step , G = 1, $C_L$ = 100 pF,	V <sub>S</sub> = 5.5 V		2		μs
	Overload recovery time	V <sub>IN</sub> × Gain > V <sub>S</sub>			0.33		μs
THD+N	THD + noise	$V_O = 1 V_{RMS}$ , G = 1, f = 1 kHz, $R_L = 10$	) kΩ	0	.00027%		
OUTPUT	Ī						
		R <sub>L</sub> = 10 kΩ	T <sub>A</sub> = 25°C		10	20	mV
	Voltage output swing from rail	T( 10 K22	$T_A = -40^{\circ}C \text{ to } +125^{\circ}C$			40	mV
	voltage output swing from rail	$R_L = 2 k\Omega$	T <sub>A</sub> = 25°C		40	50	mV
		11 - 2 112	$T_A = -40^{\circ}C \text{ to } +125^{\circ}C$			80	mV
I <sub>SC</sub>	Short-circuit current				30 / –50		mA
$C_{LOAD}$	Capacitive load drive			See	Section 6.8		
R <sub>O</sub>	Open-loop output impedance				150		Ω
POWER	SUPPLY						
Vs	Specified voltage			2.2		5.5	V
	Operating voltage				2 to 5.5		V
lo	Oujescent current per amplifier	I <sub>O</sub> = 0, V <sub>S</sub> = 5.5 V, V <sub>CM</sub> < (V+) – 1.3 V	T <sub>A</sub> = 25°C		760	950	μΑ
IQ	Quiescent current per ampliner	10 - 0, v <sub>S</sub> - 3.5 v, v <sub>CM</sub> \ (v <sub>T</sub> ) - 1.3 v	$T_A = -40^{\circ}C \text{ to } +125^{\circ}C$			1	mA



## 6.8 Typical Characteristics



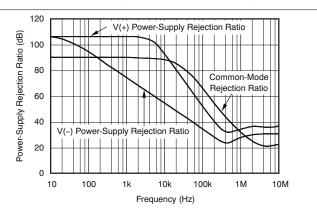
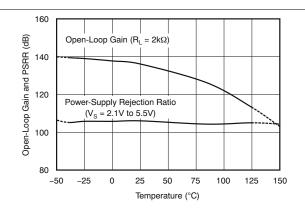


Figure 6-1. Open-Loop Gain and Phase vs Frequency

Figure 6-2. Power-Supply and Common-Mode Rejection Ratio vs Frequency



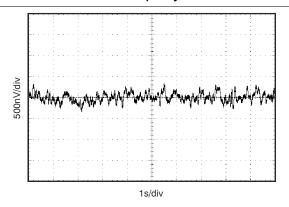
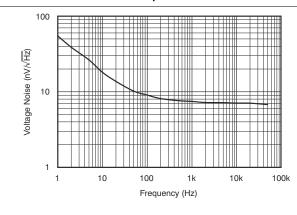


Figure 6-3. Open-Loop Gain and Power-Supply Rejection Ratio vs Temperature

Figure 6-4. 0.1-Hz to 10-Hz Input Voltage Noise



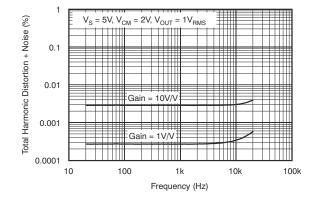
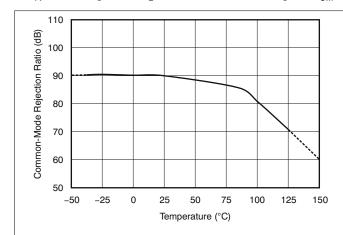


Figure 6-5. Input Voltage Noise Spectral Density

Figure 6-6. Total Harmonic Distortion + Noise vs Frequency



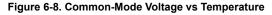
# **6.8 Typical Characteristics (continued)**

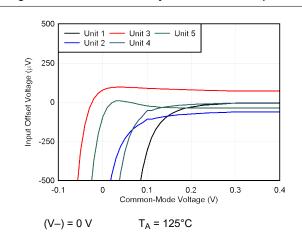


3.6 (V+) - 1.3 V3.2 Common-Mode Voltage (V) 2.8 2.4 2  $V_{\text{CM+}}$  $V_{CM}$ 1.6 1.2 0.8 (V-) + 0.4 V0.4 -40 -25 -10 20 35 50 65 80 95 110 125 Temperature (

 $V_{CM}$  range for typical CMRR = 90 dB

Figure 6-7. Common-Mode Rejection Ratio vs Temperature





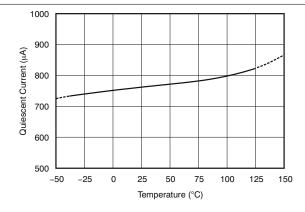
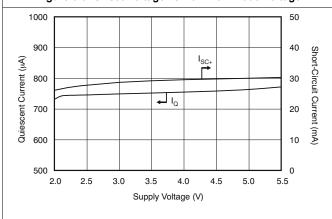


Figure 6-9. Offset Voltage vs Common-Mode Voltage

Figure 6-10. Quiescent Current vs Temperature



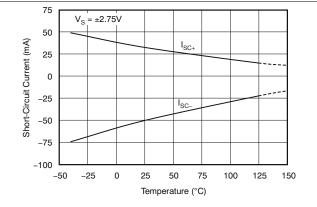
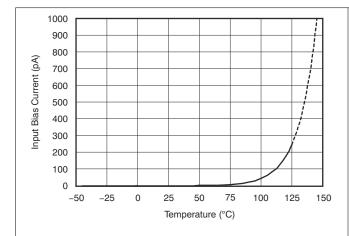


Figure 6-11. Quiescent and Short-Circuit Current vs Supply Voltage

Figure 6-12. Short-Circuit Current vs Temperature



# **6.8 Typical Characteristics (continued)**



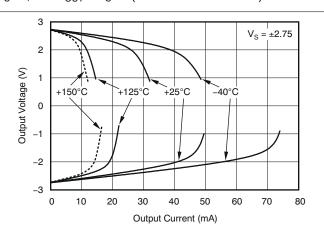
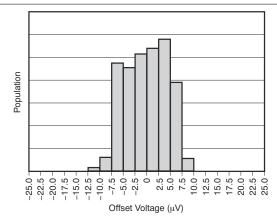


Figure 6-13. Input Bias Current vs Temperature

Figure 6-14. Output Voltage vs Output Current



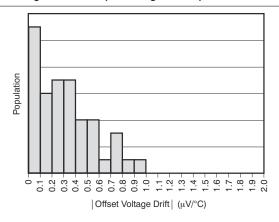
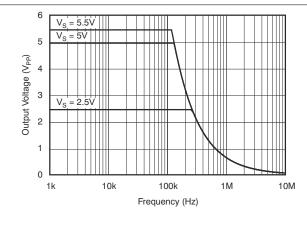


Figure 6-15. Offset Voltage Production Distribution

Figure 6-16. Offset Voltage Drift Production Distribution (-40°C to +125°C)



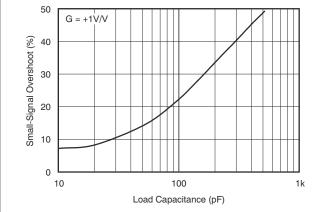
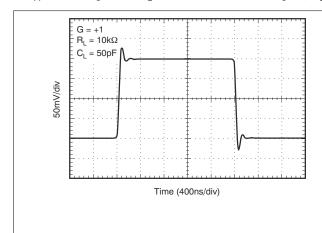


Figure 6-17. Maximum Output Voltage vs Frequency

Figure 6-18. Small-Signal Overshoot vs Load Capacitance



# **6.8 Typical Characteristics (continued)**



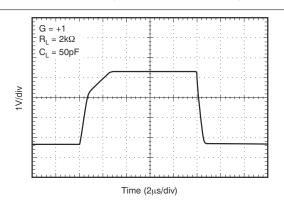
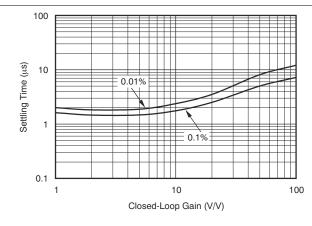


Figure 6-19. Small-Signal Pulse Response

Figure 6-20. Large-Signal Pulse Response



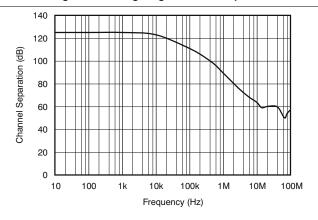


Figure 6-21. Settling Time vs Closed-Loop Gain

Figure 6-22. Channel Separation vs Frequency

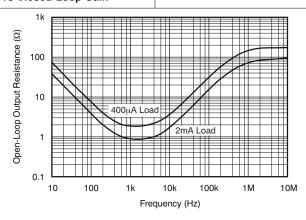


Figure 6-23. Open-Loop Output Resistance vs Frequency

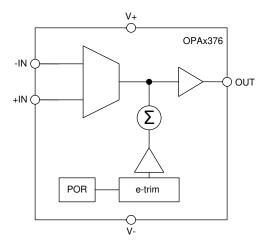


# 7 Detailed Description

#### 7.1 Overview

The OPAx376-Q1 family belongs to a new generation of low-noise e-trim operational amplifiers, giving customers outstanding dc precision and ac performance. Low noise, rail-to-rail input and output, low offset, and drawing a low quiescent current, make these devices an excellent choice for a variety of precision and portable applications. In addition, these devices have a wide supply range with excellent PSRR, making the OPAx376-Q1 a great option for applications that are battery powered without regulation.

## 7.2 Functional Block Diagram



## 7.3 Feature Description

The OPAx376-Q1 family of precision amplifiers offers excellent dc performance as well as excellent ac performance. Operating from a single power-supply the OPAx376-Q1 is capable of driving large capacitive loads, has a wide input common-mode voltage range, and is well-suited to drive the inputs of successive-approximation response (SAR) analog-to-digital converters (ADCs) as well as 24-bit and higher resolution converters. Including internal ESD protection, the OPAx376-Q1 family is offered in a variety of industry-standard packages, including a wafer chip-scale package for applications that require space savings.

#### 7.3.1 Operating Voltage

The OPAx376-Q1 family of amplifiers operate over a power-supply range of 2.2 V to 5.5 V (±1.1 V to ±2.75 V). Many of the specifications apply from –40°C to +125°C. Parameters that can exhibit significant variance with regard to operating voltage or temperature are presented in *Section 6.8*.

# 7.3.2 Input Offset Voltage and Input Offset Voltage Drift

The OPAx376-Q1 family of e-trim operational amplifiers is manufactured using TI's proprietary trim technology, a method of trimming internal device parameters during either wafer probing or final testing. Each amplifier is trimmed in production, thereby minimizing errors associated with input offset voltage and input offset voltage drift.

### 7.3.3 Capacitive Load and Stability

The OPAx376-Q1 series of amplifiers may be used in applications where driving a capacitive load is required. As with all op amps, there may be specific instances where the OPAx376-Q1 can become unstable, leading to oscillation. The particular op amp circuit configuration, layout, gain, and output loading are some of the factors to consider when establishing whether an amplifier is be stable in operation. An op amp in the unity-gain (1 V/V) buffer configuration and driving a capacitive load exhibits a greater tendency to be unstable than an amplifier operated at a higher noise gain. The capacitive load, in conjunction with the op amp output resistance, creates a pole within the feedback loop that degrades the phase margin. The degradation of the phase margin increases as the capacitive loading increases.

The OPAx376 in a unity-gain configuration can directly drive up to 250 pF of pure capacitive load. Increasing the gain enhances the ability of the amplifier to drive greater capacitive loads; see the typical characteristic plot Figure 6-18, Small-Signal Overshoot vs Load Capacitance. In unity-gain configurations, capacitive load drive can be improved by inserting a small ( $10-\Omega$  to  $20-\Omega$ ) resistor,  $R_S$ , in series with the output, as shown in Figure 7-1. This resistor significantly reduces ringing while maintaining dc performance for purely capacitive loads. However, if there is a resistive load in parallel with the capacitive load, a voltage divider is created, introducing a gain error at the output and slightly reducing the output swing. The error introduced is proportional to the ratio  $R_S$  /  $R_L$ , and is generally negligible at low output current levels.

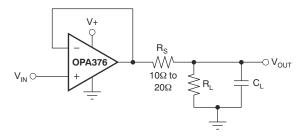


Figure 7-1. Improving Capacitive Load Drive

#### 7.3.4 Common-Mode Voltage Range

The input common-mode voltage range of the OPAx376-Q1 series extends 100 mV beyond the supply rails. The offset voltage of the amplifier is very low, from approximately (V-) to (V+)-1 V, as shown in Figure 7-2. The offset voltage increases as common-mode voltage exceeds (V+)-1 V. Common-mode rejection is specified from (V-) to (V+)-1.3 V.

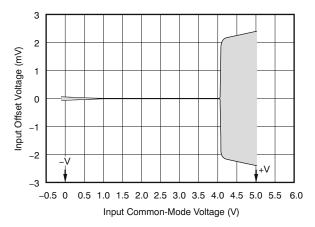


Figure 7-2. Offset and Common-Mode Voltage



#### 7.3.5 Input and ESD Protection

The OPAx376-Q1 family incorporates internal electrostatic discharge (ESD) protection circuits on all pins. In the case of input and output pins, this protection primarily consists of current steering diodes connected between the input and power-supply pins. These ESD protection diodes also provide in-circuit, input overdrive protection, as long as the current is limited to 10 mA as stated in *Section 6.1*.

Figure 7-3 shows how a series input resistor may be added to the driven input to limit the input current. The added resistor contributes thermal noise at the amplifier input and its value must be kept to a minimum in noise-sensitive applications.

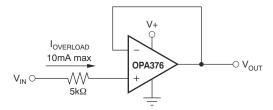


Figure 7-3. Input Current Protection

#### 7.4 Device Functional Modes

The OPAx376-Q1 has a single functional mode and is operational when the power-supply voltage is greater than 2.2 V (±1.1 V). The maximum power supply voltage for the OPAx376-Q1 is 5.5 V (±2.75 V).

# 8 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 8.1 Application Information

The OPAx376-Q1 family of e-trim operational amplifiers is built using a proprietary technique in which offset voltage is adjusted during the final steps of manufacturing. This technique compensates for performance shifts that can occur during the molding process. Through e-trim operational amplifier technology, the OPAx376-Q1 family delivers excellent offset voltage (5  $\mu$ V, typical). Additionally, the amplifier boasts a fast slew rate, low drift, low noise, and excellent PSRR and A<sub>OL</sub>. These 5.5-MHz CMOS op amps operate on 760  $\mu$ A (typical) quiescent current.

# 8.1.1 Basic Amplifier Configurations

The OPAx376-Q1 family is unity-gain stable. It does not exhibit output phase inversion when the input is overdriven. A typical single-supply connection is shown in Figure 8-1. The OPA376-Q1 is configured as a basic inverting amplifier with a gain of -10 V/V. This single-supply connection has an output centered on the common-mode voltage,  $V_{CM}$ . For the circuit shown in Figure 8-1, this voltage is 2.5 V, but may be any value within the common-mode input voltage range.

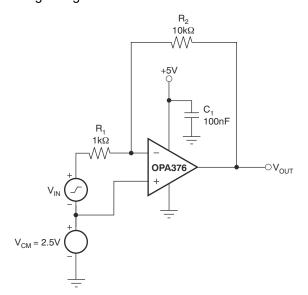


Figure 8-1. Basic Single-Supply Connection



#### 8.1.2 Active Filtering

The OPA376-Q1 series is well-suited for filter applications requiring a wide bandwidth, fast slew rate, low-noise, single-supply operational amplifier. Figure 8-2 shows a 50-kHz, second-order, low-pass filter. The components have been selected to provide a maximally-flat Butterworth response. Beyond the cutoff frequency, roll-off is –40 dB/dec. The Butterworth response is ideal for applications requiring predictable gain characteristics such as the anti-aliasing filter used ahead of an ADC.

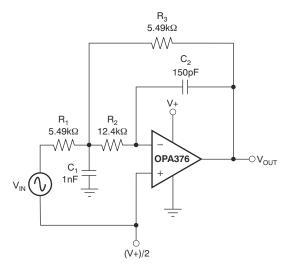
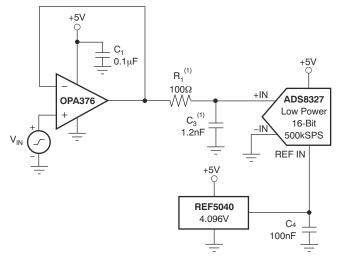


Figure 8-2. Second-Order Butterworth, 50-kHz Low-Pass Filter

#### 8.1.3 Driving an Analog-to-Digital Converter

The low noise and wide gain bandwidth of the OPA376-Q1 family make it an ideal driver for ADCs. Figure 8-3 illustrates the OPA376-Q1 driving an ADS8327, 16-bit, 250-kSPS converter. The amplifier is connected as a unity-gain, noninverting buffer.



(1) Suggested value; may require adjustment based on specific application.

Figure 8-3. Driving an ADS8327

## 8.1.4 Phantom-Powered Microphone

The circuit shown in Figure 8-4 depicts how a remote microphone amplifier can be powered by a phantom source on the output side of the signal cable. The cable serves double duty, carrying both the differential output signal from and dc power to the microphone amplifier stage.

An OPA2376-Q1 serves as a single-ended input to a differential output amplifier with a 6-dB gain. Common-mode bias for the two op amps is provided by the dc voltage developed across the electret microphone element. A 48-V phantom supply is reduced to 5.1 V by the series 6.8-k $\Omega$  resistors on the output side of the cable, and the 4.7-k $\Omega$  resistors and zener diode on the input side of the cable. AC coupling blocks the different dc voltage levels from each other on each end of the cable.

An INA163 instrumentation amplifier provides differential inputs and receives the balanced audio signals from the cable.

The INA163 gain may be set from 0 dB to 80 dB by selecting the  $R_G$  value. The INA163 circuit is typical of the input circuitry used in mixing consoles.

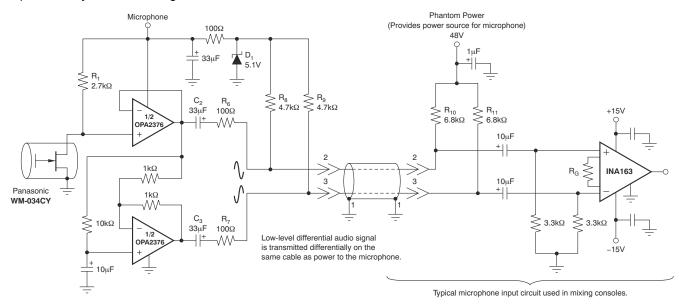
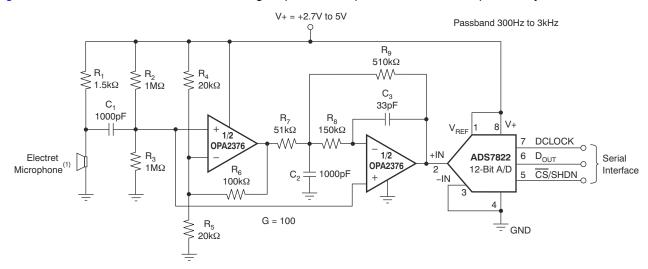


Figure 8-4. Phantom-Powered Electret Microphone

## 8.1.5 Speech Bandpass-Filtered Data Acquisition System

Figure 8-5 illustrates the OPA2376-Q1 driving a speech bandpass-filtered data acquisition system.



(1) Electret microphone powered by R<sub>1</sub>.

Figure 8-5. OPA2376-Q1 as a Speech Bandpass-Filtered Data Acquisition System

# 8.2 Typical Application

Low-pass filters are commonly employed in signal processing applications to reduce noise and prevent aliasing. The OPA376-Q1 is ideally suited to construct high-speed, high-precision active filters. Figure 8-6 shows a second-order, low-pass filter commonly encountered in signal processing applications.

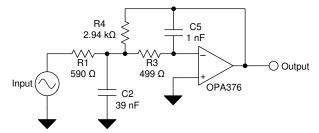


Figure 8-6. Typical Application Schematic



#### 8.2.1 Design Requirements

Use the following parameters for this design example:

- Gain = 5 V/V (inverting gain)
- Low-pass cutoff frequency = 25 kHz
- · Second-order Chebyshev filter response with 3-dB gain peaking in the passband

### 8.2.2 Detailed Design Procedure

The infinite-gain multiple-feedback circuit for a low-pass network function is shown in Figure 8-6. Use Equation 1 to calculate the voltage transfer function.

$$\frac{\text{Output}}{\text{Input}}(s) = \frac{-1/R_1R_3C_2C_5}{s^2 + (s/C_2)(1/R_1 + 1/R_3 + 1/R_4) + 1/R_3R_4C_2C_5} \tag{1}$$

This circuit produces a signal inversion. For this circuit, the gain at dc and the low-pass cutoff frequency are calculated by Equation 2:

Gain = 
$$\frac{R_4}{R_1}$$
  
 $f_C = \frac{1}{2\pi} \sqrt{(1/R_3 R_4 C_2 C_5)}$  (2)

Software tools are readily available to simplify filter design. WEBENCH® Filter Designer is a simple, powerful, and easy-to-use active filter design program. The WEBENCH Filter Designer lets you create optimized filter designs using a selection of TI operational amplifiers and passive components from TI's vendor partners.

Available as a web-based tool from the WEBENCH® Design Center, WEBENCH® Filter Designer allows you to design, optimize, and simulate complete multi-stage active filter solutions within minutes.

#### 8.2.3 Application Curve

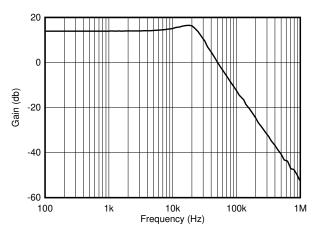


Figure 8-7. Low-Pass Filter Transfer Function

# 9 Power Supply Recommendations

The OPAx376-Q1 family of devices is specified for operation from 2.2 V to 5.5 V (±1.1 V to ±2.75 V); many specifications apply from –40°C to +125°C. Parameters that can exhibit significant variance with regard to operating voltage or temperature are presented in Section 6.8.



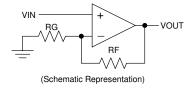
# 10 Layout

# 10.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and op amp itself.
   Bypass capacitors are used to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
  - Connect low-ESR, 0.1-μF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for singlesupply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective
  methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes.
  A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital
  and analog grounds paying attention to the flow of the ground current. For more detailed information refer to
  the Circuit Board Layout Techniques application report.
- In order to reduce parasitic coupling, run the input traces as far away from the supply or output traces as
  possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicular is much better as
  opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. As shown in Figure 10-1, keeping RF and RG close to the inverting input minimizes parasitic capacitance.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.
- Cleaning the PCB following board assembly is recommended for best performance.
- Any precision integrated circuit may experience performance shifts due to moisture ingress into the plastic package. Following any aqueous PCB cleaning process, baking the PCB assembly is recommended to remove moisture introduced into the device packaging during the cleaning process. A low-temperature, post-cleaning bake at 85°C for 30 minutes is sufficient for most circumstances.

#### 10.2 Layout Example



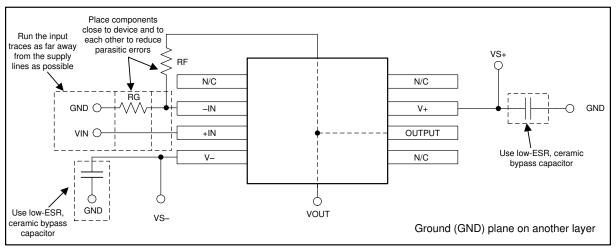


Figure 10-1. Layout Example



# 11 Device and Documentation Support

# 11.1 Device Support

### 11.1.1 Development Support

#### 11.1.1.1 TINA-TI™ Simulation Software (Free Download)

TINA™ is a simple, powerful, and easy-to-use circuit simulation program based on a SPICE engine. TINA-TI™ simulation software is a free, fully-functional version of the TINA software, preloaded with a library of macro models in addition to a range of both passive and active models. TINA-TI simulation software provides all the conventional dc, transient, and frequency domain analysis of SPICE, as well as additional design capabilities.

Available as a free download from the Analog eLab Design Center, TINA-TI simulation software offers extensive post-processing capability that allows users to format results in a variety of ways. Virtual instruments offer the ability to select input waveforms and probe circuit nodes, voltages, and waveforms, creating a dynamic quick-start tool.

#### Note

These files require that either the TINA software (from DesignSoft<sup>™</sup>) or TINA-TI software be installed. Download the free TINA-TI software from the TINA-TI folder.

# 11.1.1.2 TI Precision Designs

TI Precision Designs are analog solutions created by TI's precision analog applications experts and offer the theory of operation, component selection, simulation, complete PCB schematic and layout, bill of materials, and measured performance of many useful circuits. TI Precision Designs are available online at <a href="http://www.ti.com/ww/en/analog/precision-designs/">http://www.ti.com/ww/en/analog/precision-designs/</a>.

#### 11.1.1.3 WEBENCH® Filter Designer

WEBENCH® Filter Designer is a simple, powerful, and easy-to-use active filter design program. The WEBENCH® Filter Designer lets you create optimized filter designs using a selection of TI operational amplifiers and passive components from TI's vendor partners.

Available as a web-based tool from the WEBENCH® Design Center, WEBENCH® Filter Designer allows you to design, optimize, and simulate complete multistage active filter solutions within minutes.

#### 11.2 Documentation Support

#### 11.2.1 Related Documentation

For related documentation see the following:

- Texas Instruments, INA163 Low-Noise, Low-Distortion Instrumentation Amplifier data sheet
- Texas Instruments, Operational Amplifier Gain stability, Part 3: AC Gain-Error Analysis
- · Texas Instruments, Operational Amplifier Gain Stability, Part 2: DC Gain-Error Analysis
- Texas Instruments, Op Amp Performance Analysis
- Texas Instruments, Shelf-Life Evaluation of Lead-Free Component Finishes
- Texas Instruments, Single-Supply Operation of Operational Amplifiers
- Texas Instruments, Tuning in Amplifiers
- Texas Instruments, Using Infinite-Gain, MFB Filter Topology in Fully Differential Active Filters

## 11.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

## 11.4 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.



Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 11.5 Trademarks

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WEBENCH® is a registered trademark of Texas Instruments.

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#### 11.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 11.7 Glossary

**TI Glossary** 

This glossary lists and explains terms, acronyms, and definitions.

# 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 9-Nov-2025

#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
OPA2376AQDRQ1	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	2376Q1
OPA2376AQDRQ1.A	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	2376Q1
OPA2376AQDRQ1.B	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	2376Q1
OPA2376QDGKRQ1	Active	Production	VSSOP (DGK)   8	2500   LARGE T&R	Yes	NIPDAU   NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	2376
OPA2376QDGKRQ1.A	Active	Production	VSSOP (DGK)   8	2500   LARGE T&R	Yes	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	2376
OPA2376QDGKRQ1.B	Active	Production	VSSOP (DGK)   8	2500   LARGE T&R	Yes	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	2376
OPA376AQDBVRQ1	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	OUHQ
OPA376AQDBVRQ1.A	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	OUHQ
OPA376AQDBVRQ1G4	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	OUHQ
OPA376AQDBVRQ1G4.A	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	OUHQ
OPA4376AQPWRQ1	Active	Production	TSSOP (PW)   14	2000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	4376Q1
OPA4376AQPWRQ1.B	Active	Production	TSSOP (PW)   14	2000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	4376Q1

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

# **PACKAGE OPTION ADDENDUM**

www.ti.com 9-Nov-2025

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#### OTHER QUALIFIED VERSIONS OF OPA2376-Q1, OPA376-Q1, OPA4376-Q1:

Catalog: OPA2376, OPA376, OPA4376

NOTE: Qualified Version Definitions:

Catalog - TI's standard catalog product

# **PACKAGE MATERIALS INFORMATION**

www.ti.com 10-Sep-2025

## TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
OPA2376AQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA2376QDGKRQ1	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
OPA376AQDBVRQ1	SOT-23	DBV	5	3000	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
OPA376AQDBVRQ1G4	SOT-23	DBV	5	3000	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
OPA4376AQPWRQ1	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1



www.ti.com 10-Sep-2025



\*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
OPA2376AQDRQ1	SOIC	D	8	2500	353.0	353.0	32.0
OPA2376QDGKRQ1	VSSOP	DGK	8	2500	353.0	353.0	32.0
OPA376AQDBVRQ1	SOT-23	DBV	5	3000	213.0	191.0	35.0
OPA376AQDBVRQ1G4	SOT-23	DBV	5	3000	213.0	191.0	35.0
OPA4376AQPWRQ1	TSSOP	PW	14	2000	353.0	353.0	32.0



SMALL OUTLINE INTEGRATED CIRCUIT



## NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE TRANSISTOR



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
  3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







#### NOTES:

PowerPAD is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187.





NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
- 9. Size of metal pad may vary due to creepage requirement.





NOTES: (continued)

- 11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 12. Board assembly site may have different recommendations for stencil design.



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